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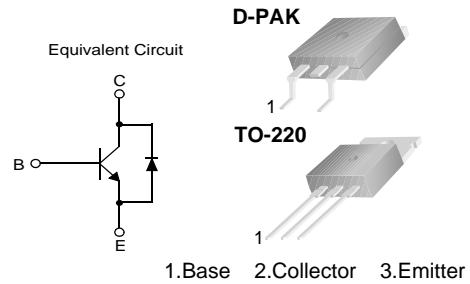
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# KSC5402D/KSC5402DT

## NPN Silicon Transistor, Planar Silicon Transistor

### Features

- High Voltage High Speed Power Switch Application
- Wide Safe Operating Area
- Built-in Free Wheeling Diode
- Suitable for Electronic Ballast Application
- Small Variance in Storage Time
- Two Package Choices; D-PAK or TO-220



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	1000	V
$V_{CEO}$	Collector-Emitter Voltage	450	V
$V_{EBO}$	Emitter-Base Voltage	12	V
$I_C$	Collector Current (DC)	2	A
$I_{CP}$	*Collector Current (Pulse)	5	A
$I_B$	Base Current (DC)	1	A
$I_{BP}$	*Base Current (Pulse)	2	A
$P_C$	Power Dissipation( $T_C=25^\circ\text{C}$ ) : D-PAK* : TO-220	30 50	W W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	- 65 to 150	$^\circ\text{C}$

\* Pulse Test: Pulse Width=5ms, Duty Cycle $\leq$ 10%

### Thermal Characteristics $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating		Units	
		TO-220	D-PAK		
$R_{\theta JC}$	Thermal Resistance	Junction to Case	2.5	4.17*	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$		Junction to Ambient	62.5	50	$^\circ\text{C}/\text{W}$
$T_L$	Maximum Lead Temperature for Soldering Purpose ; 1/8" from Case for 5 Seconds		270	270	$^\circ\text{C}$

\* Mounted on 1" square PCB (FR4 ro G-10 Material)

**Electrical Characteristics**  $T_A=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}, I_E=0$	1000	1090		V
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}, I_B=0$	450	525		V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}, I_C=0$	12	14		V
$I_{CES}$	Collector Cut-off Current	$V_{CES}=1000\text{V}, I_{EB}=0$	$T_A=25^\circ\text{C}$	0.03	100	$\mu\text{A}$
			$T_A=125^\circ\text{C}$	1.2	500	$\mu\text{A}$
$I_{CEO}$	Collector Cut-off Current	$V_{CE}=450\text{V}, V_B=0$	$T_A=25^\circ\text{C}$	0.3	100	$\mu\text{A}$
			$T_A=125^\circ\text{C}$	15	500	$\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB}=10\text{V}, I_C=0$		0.01	100	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$V_{CE}=1\text{V}, I_C=0.4\text{A}$	$T_A=25^\circ\text{C}$	14	29	
			$T_A=125^\circ\text{C}$	8	17	
		$V_{CE}=1\text{V}, I_C=1\text{A}$	$T_A=25^\circ\text{C}$	6	9	
			$T_A=125^\circ\text{C}$	4	6	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=0.4, I_B=0.04\text{A}$	$T_A=25^\circ\text{C}$	0.25	0.6	V
			$T_A=125^\circ\text{C}$	0.4	1.0	V
		$I_C=1\text{A}, I_B=0.2\text{A}$	$T_A=25^\circ\text{C}$	0.3	0.75	V
			$T_A=125^\circ\text{C}$	0.65	1.2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=0.4\text{A}, I_B=0.04\text{A}$	$T_A=25^\circ\text{C}$	0.78	1.0	V
			$T_A=125^\circ\text{C}$	0.65	0.9	V
		$I_C=1\text{A}, I_B=0.2\text{A}$	$T_A=25^\circ\text{C}$	0.85	1.1	V
			$T_A=125^\circ\text{C}$	0.75	1.0	V
$C_{ib}$	Input Capacitance	$V_{EB}=8\text{V}, I_C=0, f=1\text{MHz}$		330	500	pF
$C_{ob}$	Output Capacitance	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		35	100	pF
$f_T$	Current Gain Bandwidth Product	$I_C=0.5\text{A}, V_{CE}=10\text{V}$		11		MHz
$V_F$	Diode Forward Voltage	$I_F=1\text{A}$	$T_A=25^\circ\text{C}$	0.86	1.5	V
			$T_A=125^\circ\text{C}$	0.75	1.2	V
		$I_F=0.2\text{A}$	$T_A=25^\circ\text{C}$	0.6		V
			$T_A=125^\circ\text{C}$	0.8	1.3	V
		$I_F=0.4\text{A}$	$T_A=125^\circ\text{C}$	0.65		V

**Electrical Characteristics** (Continued)  $T_A=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units	
$t_{fr}$	Diode Forward Recovery Time ( $di/dt=10\text{A}/\mu\text{s}$ )	$I_F=0.2\text{A}$		540		ns	
		$I_F=0.4\text{A}$		520		ns	
		$I_F=1\text{A}$		480		ns	
$V_{CE(DSAT)}$	Dynamic Saturation Voltage	$I_C=0.4\text{A}, I_{B1}=40\text{mA}$ $V_{CC}=300\text{V}$	@ $1\mu\text{s}$	7.5		V	
			@ $3\mu\text{s}$	2.5		V	
		$I_C=1\text{A}, I_{B1}=200\text{mA}$ $V_{CC}=300$	@ $1\mu\text{s}$	11.5		V	
			@ $3\mu\text{s}$	1.5		V	
RESISTIVE LOAD SWITCHING (D.C $\leq 10\%$ , Pulse Width= $20\mu\text{s}$ )							
$t_{ON}$	Turn On Time	$I_C=1\text{A},$ $I_{B1}=200\text{mA},$ $I_{B2}=150\text{mA},$ $V_{CC}=300\text{V},$ $R_L = 300\Omega$	$T_A=25^\circ\text{C}$		110	150	ns
			$T_A=125^\circ\text{C}$		135		ns
$t_{OFF}$	Turn Off Time		$T_A=25^\circ\text{C}$	0.95		1.25	$\mu\text{s}$
			$T_A=125^\circ\text{C}$		1.4		$\mu\text{s}$
INDUCTIVE LOAD SWITCHING ( $V_{CC}=15\text{V}$ )							
$t_{STG}$	Storage Time	$I_C=0.4\text{A},$ $I_{B1}=40\text{mA},$ $I_{B2}=200\text{mA},$ $V_Z=300\text{V},$ $L_C=200\text{H}$	$T_A=25^\circ\text{C}$		0.56	0.65	$\mu\text{s}$
			$T_A=125^\circ\text{C}$		0.7		$\mu\text{s}$
$t_F$	Fall Time		$T_A=25^\circ\text{C}$		60	175	ns
			$T_A=125^\circ\text{C}$		75		ns
$t_C$	Cross-over Time		$T_A=25^\circ\text{C}$		90	175	ns
			$T_A=125^\circ\text{C}$		90		ns
$t_{STG}$	Storage Time	$I_C=0.8\text{A},$ $I_{B1}=160\text{mA},$ $I_{B2}=160\text{mA},$ $V_Z=300\text{V},$ $L_C=200\text{H}$	$T_A=25^\circ\text{C}$			2.75	$\mu\text{s}$
			$T_A=125^\circ\text{C}$		3		$\mu\text{s}$
$t_F$	Fall Time		$T_A=25^\circ\text{C}$		110	175	ns
			$T_A=125^\circ\text{C}$		180		ns
$t_C$	Cross-over Time		$T_A=25^\circ\text{C}$		125	350	ns
			$T_A=125^\circ\text{C}$		185		ns
$t_{STG}$	Storage Time	$I_C=1\text{A},$ $I_{B1}=200\text{mA},$ $I_{B2}=500\text{mA},$ $V_Z=300\text{V},$ $L_C=200\mu\text{H}$	$T_A=25^\circ\text{C}$		1.1	1.2	$\mu\text{s}$
			$T_A=125^\circ\text{C}$		1.35		$\mu\text{s}$
$t_F$	Fall Time		$T_A=25^\circ\text{C}$		105	150	ns
			$T_A=125^\circ\text{C}$		75		ns
$t_C$	Cross-over Time		$T_A=25^\circ\text{C}$		125	150	ns
			$T_A=125^\circ\text{C}$		100		ns

## Typical Performance Characteristics

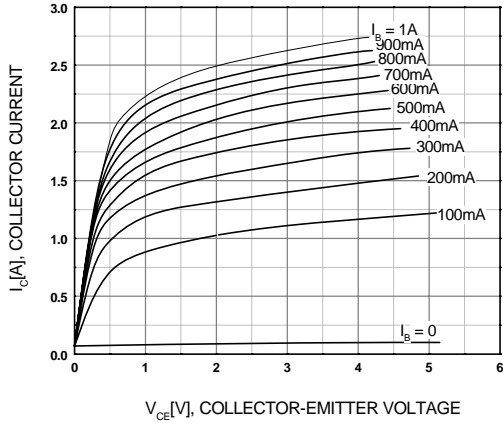


Figure 1. Static Characteristic

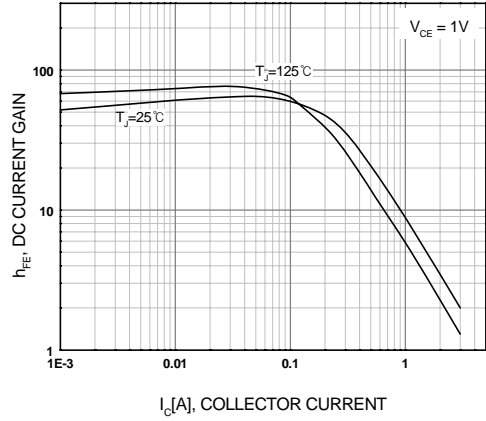


Figure 2. DC current Gain

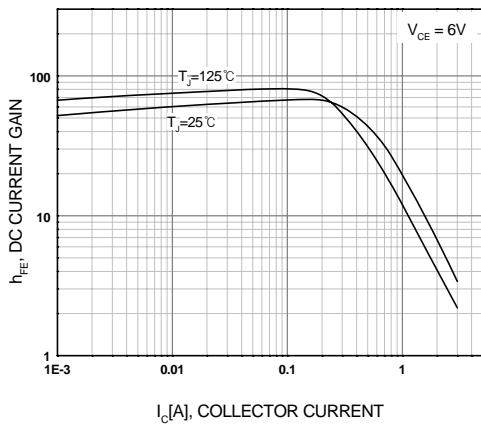


Figure 3. DC current Gain

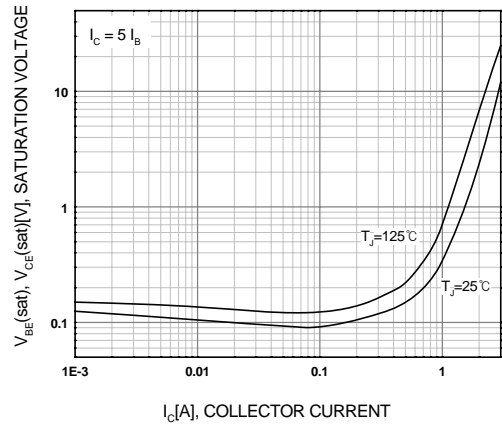


Figure 4. Collector-Emitter Saturation Voltage

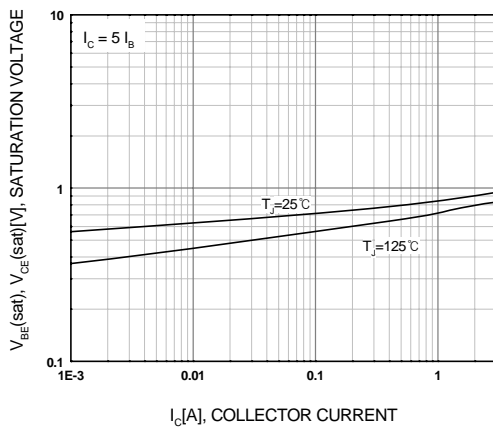


Figure 5. Base-Emitter Saturation Voltage

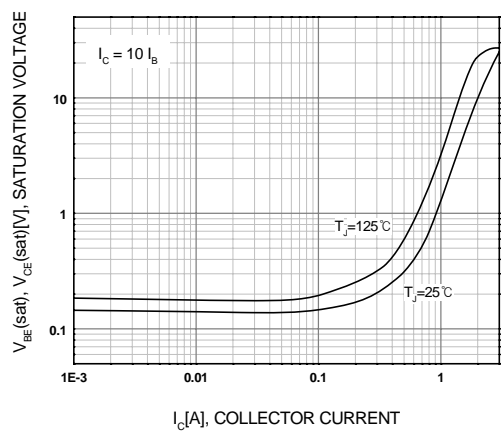
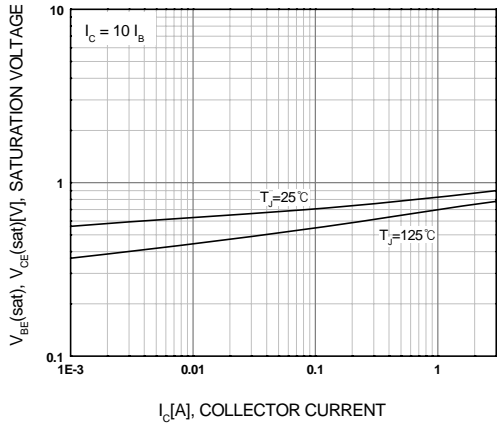
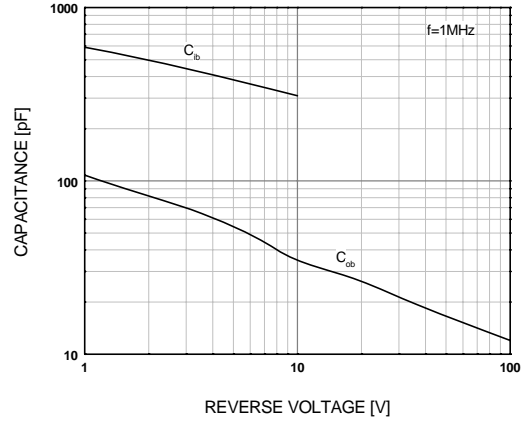


Figure 6. Collector-Emitter Saturation Voltage

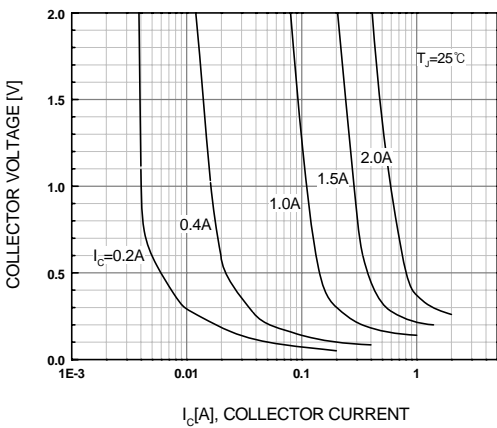
**Typical Performance Characteristics (Continued)**



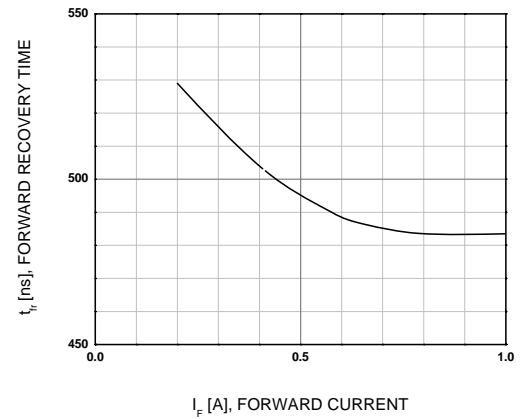
**Figure 7. Base-Emitter Saturation Voltage**



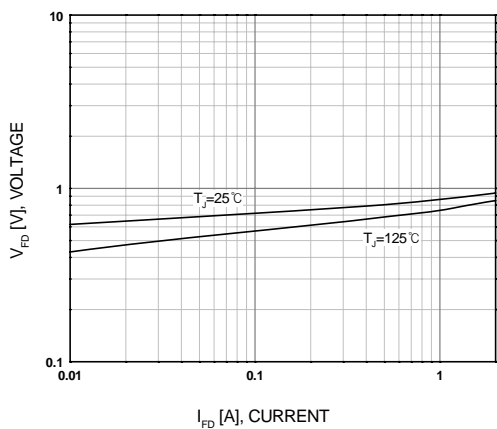
**Figure 8. Collector Output Capacitance**



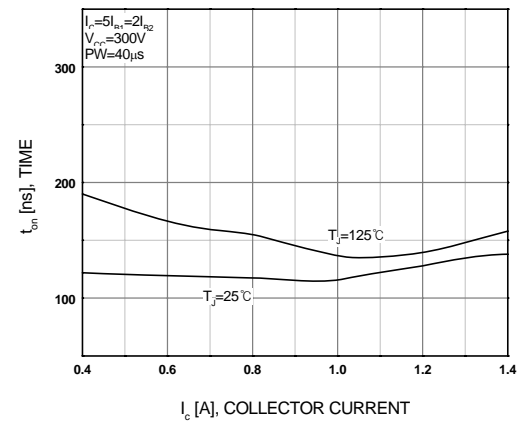
**Figure 9. Typical Collector Saturation Region**



**Figure 10. Forward Recovery Time**

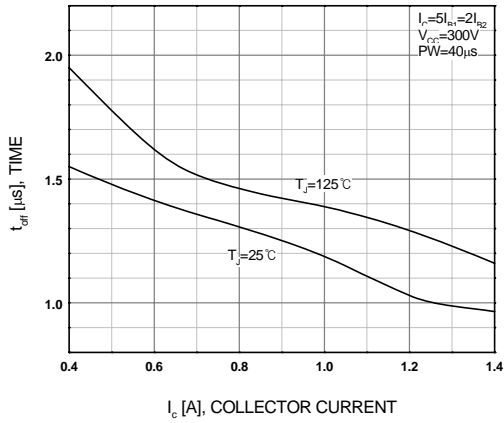


**Figure 11. Diode Forward Voltage**

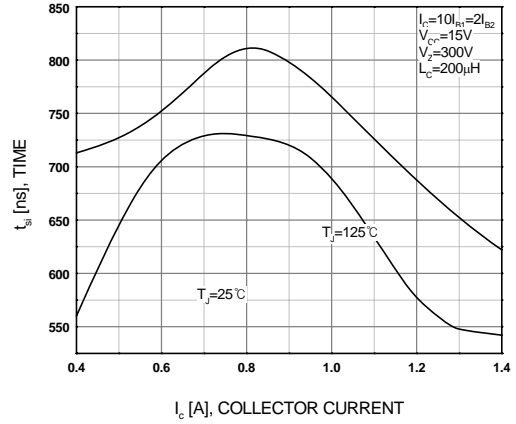


**Figure 12. Resistive Switching Time,  $t_{on}$**

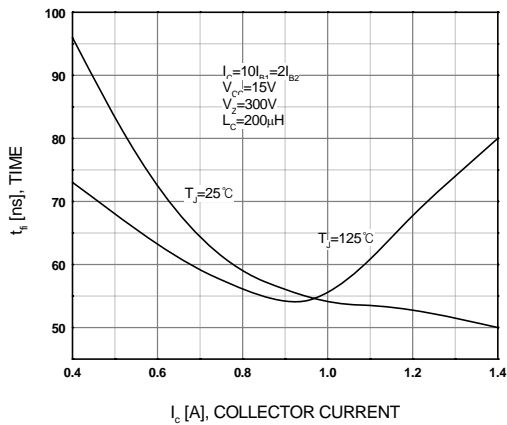
**Typical Performance Characteristics (Continued)**



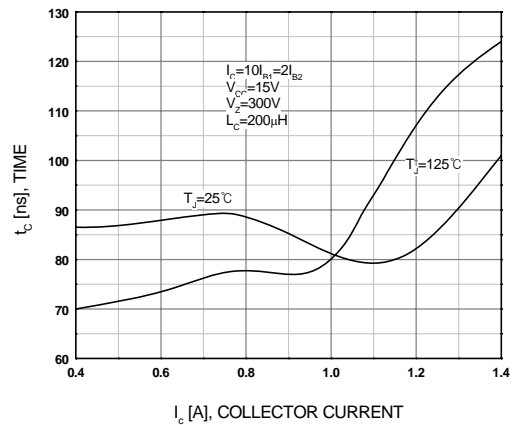
**Figure 13. Resistive Switching Time,  $t_{off}$**



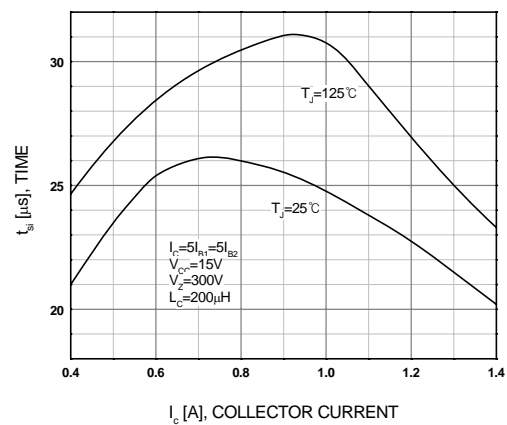
**Figure 14. Inductive Switching Time,  $t_{si}$**



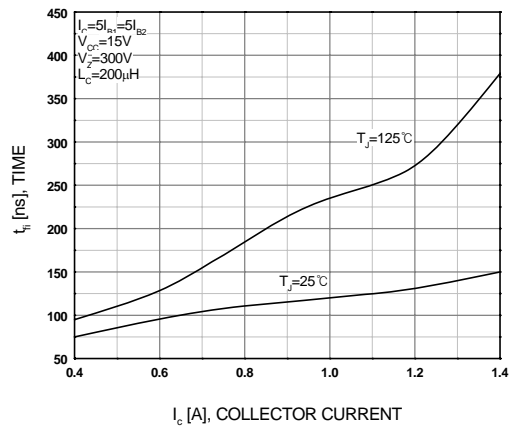
**Figure 15. Inductive Switching Time,  $t_{fi}$**



**Figure 16. Inductive Switching Time,  $t_c$**

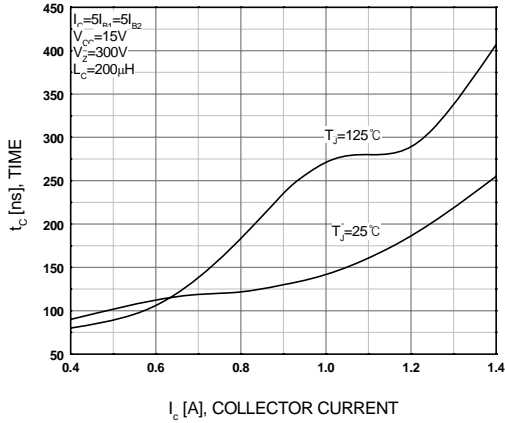


**Figure 17. Inductive Switching Time,  $t_{si}$**

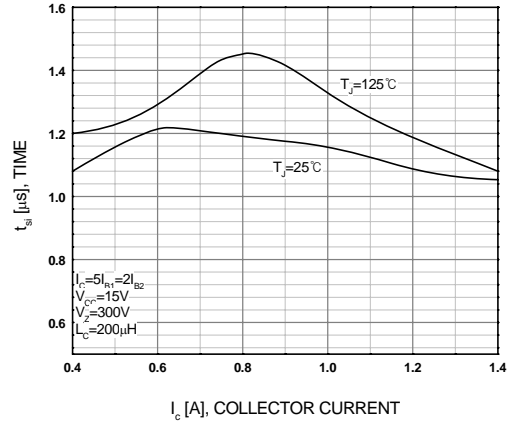


**Figure 18. Inductive Switching Time,  $t_{fi}$**

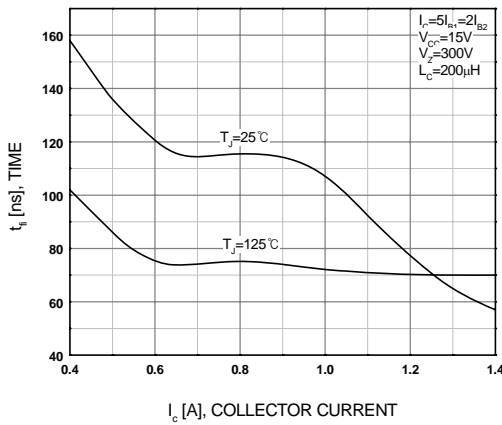
**Typical Performance Characteristics (Continued)**



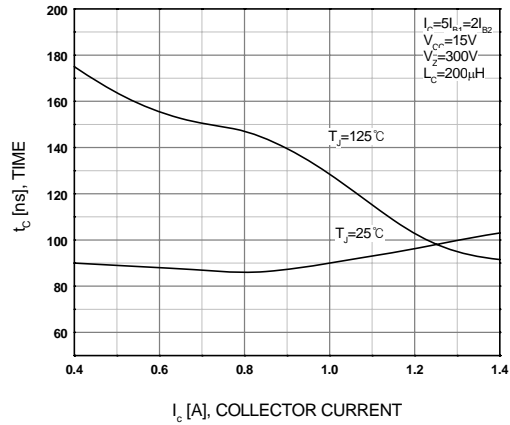
**Figure 19. Inductive Switching Time,  $t_c$**



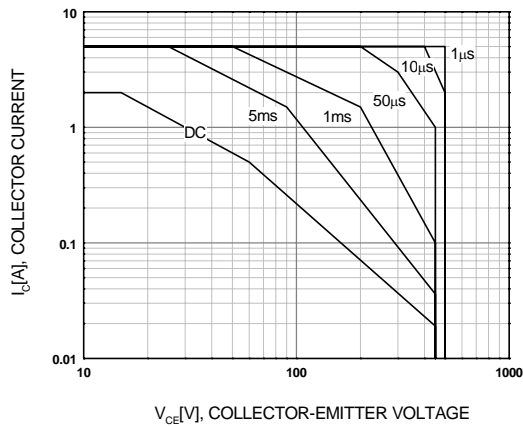
**Figure 20. Inductive Switching Time,  $t_{si}$**



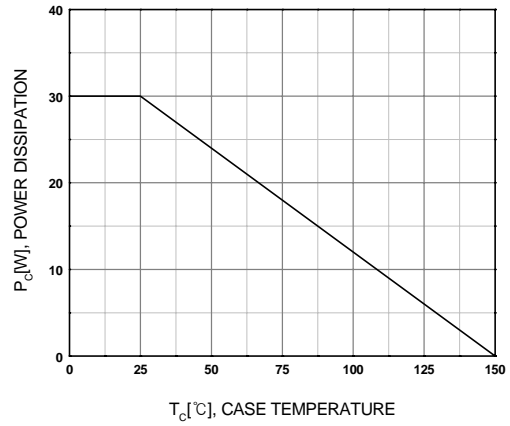
**Figure 21. Inductive Switching Time,  $t_{fi}$**



**Figure 22. Inductive Switching Time,  $t_c$**



**Figure 23. Forward Bias Safe Operating Area**

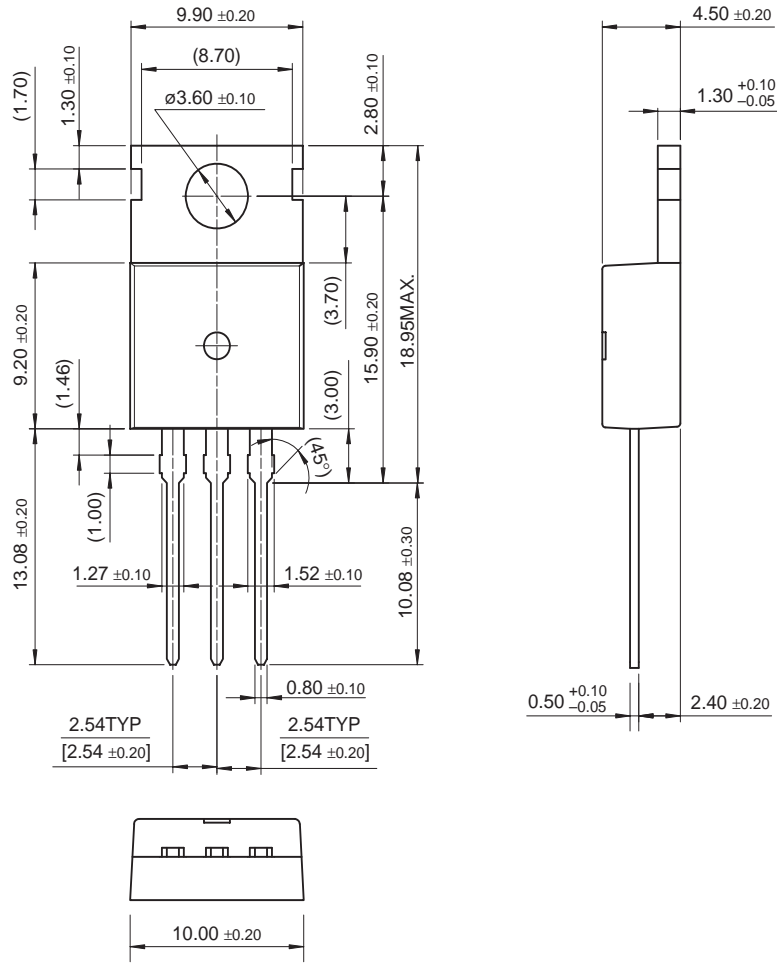


**Figure 24. Power Derating**



Physical Dimension

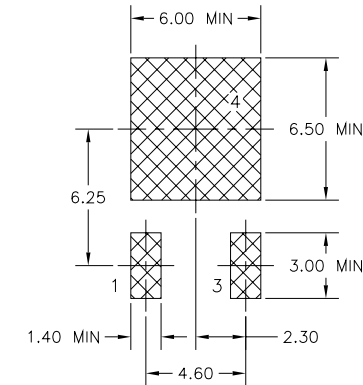
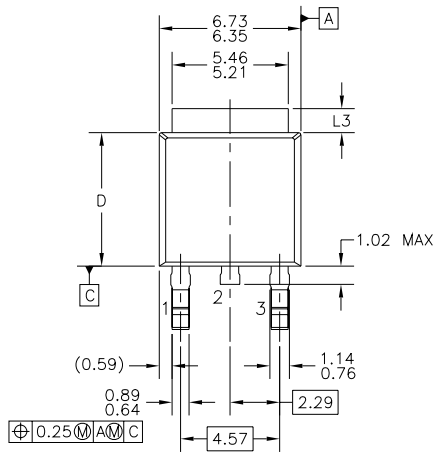
TO-220



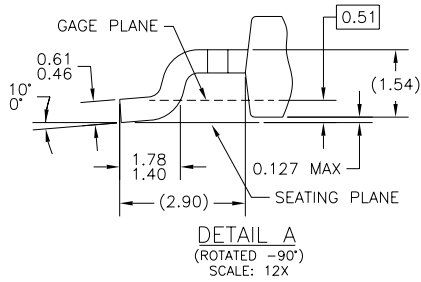
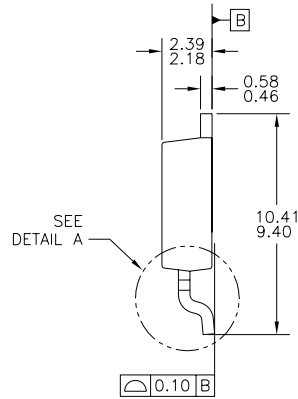
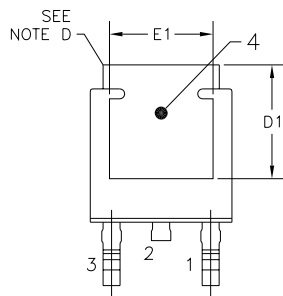
Dimensions in Millimeters

**Physical Dimension (Continued)**

**D-PAK**



LAND PATTERN RECOMMENDATION









- NOTES: UNLESS OTHERWISE SPECIFIED  
 A) ALL DIMENSIONS ARE IN MILLIMETERS.  
 B) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA & AB, DATED NOV. 1999.  
 C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.  
 D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.  
 E) DIMENSIONS L3,D,E1&D1 TABLE:
- |    | OPTION AA | OPTION AB |
|----|-----------|-----------|
| L3 | 0.89-1.27 | 1.52-2.03 |
| D  | 5.97-6.22 | 5.33-5.59 |
| E1 | 4.32 MIN  | 3.81 MIN  |
| D1 | 5.21 MIN  | 4.57 MIN  |
- F) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.

Dimensions in Millimeters



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Fairchild®	MicroPak™	SuperFET™	UHC®
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**Definition of Terms**

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